



# **PRODUCT DATA SHEET**



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Datasheet

Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO\_questions@jgsemi.com.



ESD Protection Diode Array

#### **Features**

- 60Watts peak pulse power (tp =  $8/20\mu$ s)
- SOT23-6 package
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance (Cj=0.22pF typ. IO to IO)
- Protection one data/power line to:
- IEC 61000-4-2  $\pm$ 20kV contact  $\pm$ 20kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 4A (8/20μs)



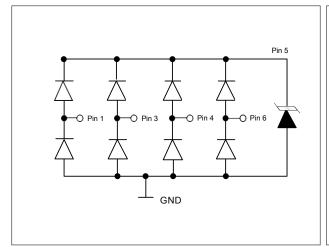
### **Applications**

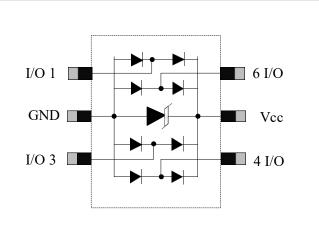
- Ethernet
- Digital Visual Interface (DVI)
- USB2.0
- Notebook and PC Computers

#### **Mechanical Data**

- SOT23-6 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

### Schematic & PIN Configuration







**Absolute Maximum Rating** 

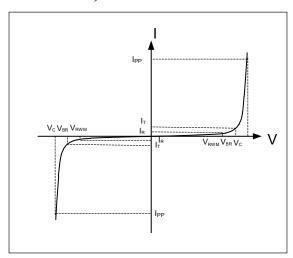
Rating	Symbol	Value	Units	
Peak Pulse Power (t <sub>p</sub> =8/20μs)	P <sub>PP</sub>	60	Watts	
Peak Pulse Current ( $t_p = 8/20\mu s$ ) (note1)	$I_{pp}$	4.0	A	
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	$V_{ESD}$	20 20	kV	
Lead Soldering Temperature	$T_{\mathrm{L}}$	260(10seconds)	${\mathbb C}$	
Junction Temperature	$T_{J}$	-55 to + 125	$^{\circ}$ C	
Storage Temperature	$T_{ m stg}$	-55 to + 125	$^{\circ}$ C	

#### **Electrical Characteristics**

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	$V_{RWM}$				5.0	V
Reverse Breakdown Voltage	$V_{BR}$	I <sub>T</sub> =1mA	6			V
Reverse Leakage Current	$I_R$	V <sub>RWM</sub> =5V,T=25℃			500	nA
Peak Pulse Current	$I_{PP}$	tp =8/20μs			4.0	A
Clamping Voltage	$V_{\rm C}$	$I_{PP}=4.0A, t_p=8/20\mu s$			15	V
Junction Capacitance	$C_j$	$V_R = 0V$ , $f = 1MHz$ IO to IO		0.22	0.4	pF
		$V_R = 0V$ , $f = 1MHz$ IO to GND		0.45	0.8	

# **Electrical Parameters (TA = 25°C unless otherwise noted)**

Symbol	Parameter
$\mathbf{I}_{\text{PP}}$	Maximum Reverse Peak Pulse Current
$V_{\rm C}$	Clamping Voltage @ IPP
V <sub>RWM</sub>	Working Peak Reverse Voltage
IR	Maximum Reverse Leakage Current @ VRWM
$V_{BR}$	Breakdown Voltage @ IT
Iт	Test Current



Note:.  $8/20\mu s$  pulse waveform.



# **Typical Characteristic Curves**

Fig.1 Peak Pulse Power Rating Curve

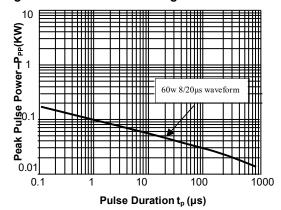


Fig.3 Pulse Waveform-8/20µs

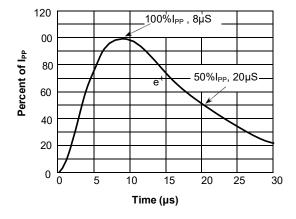


Fig.2 Pulse Derating Curve

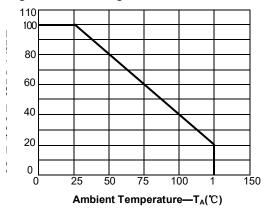
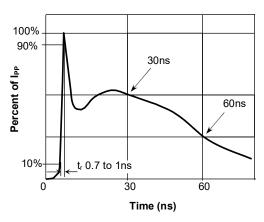


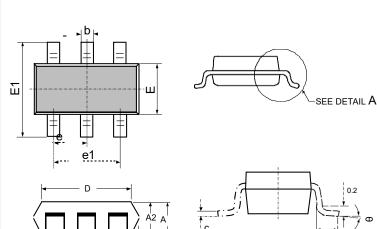
Fig.4 Pulse Waveform-ESD(IEC61000-4-2)





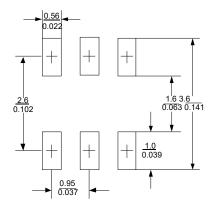
# **Outline Drawing – SOT23-6**

# **PACKAGE OUTLINE**



DIMENSIONS						
SYMBOL	INCHES		MILLIMETER			
	MIN	MAX	MIN	MAX		
Α	0.041	0.049	1.050	1.250		
A1	0.000	0.004	0.000	0.100		
A2	0.041	0.045	1.050	1.150		
D	0.111	0.119	2.820	3.020		
E	0.059	0.067	1.500	1.700		
E1	0.104	0.116	2.650	2.950		
b	0.012	0.020	0.300	0.500		
е	0.037(BSC)		0.950(BSC)			
e1	0.071	0.079	1.800	2.000		
L	0.012	0.024	0.300	0.600		
θ	0°	8°	0°	8°		





Notes

1. This land pattern is for reference purposes only consult your manufacturing group to ensure your company's manufacturing guidelines are met.



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